

Michael Oestreich

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/270162/publications.pdf>

Version: 2024-02-01

115
papers

3,917
citations

126907
33
h-index

123424
61
g-index

119
all docs

119
docs citations

119
times ranked

2417
citing authors

#	ARTICLE	IF	CITATIONS
1	Non-equilibrium spin noise spectroscopy of a single quantum dot operating at fiber telecommunication wavelengths. <i>Journal of Applied Physics</i> , 2022, 131, 065703.	2.5	1
2	Low Temperature Relaxation of Donor Bound Electron Spins in Si ₂₈ P. <i>Physical Review Letters</i> , 2021, 126, 137402.	7.8	1
3	Room Temperature Micro-Photoluminescence Studies of Colloidal WS ₂ Nanosheets. <i>Journal of Physical Chemistry C</i> , 2021, 125, 18841-18848.	3.1	7
4	Separating the two polarities of the POLO contacts of an 26.1%-efficient IBC solar cell. <i>Scientific Reports</i> , 2020, 10, 658.	3.3	66
5	Doping and temperature dependence of nuclear spin relaxation in n-type GaAs. <i>Physical Review B</i> , 2020, 102, .	3.2	0
6	Impact of optically induced carriers on the spin relaxation of localized electron spins in isotopically enriched silicon. <i>Physical Review B</i> , 2019, 99, .	3.2	1
7	From PERC to Tandem: POLO- and p ⁺ +n ⁺ /n ⁺ +p ⁺ Poly-Si Tunneling Junction as Interface Between Bottom and Top Cell. <i>IEEE Journal of Photovoltaics</i> , 2019, 9, 49-54.	2.5	29
8	Optical Amplification of Spin Noise Spectroscopy via Homodyne Detection. <i>Physical Review Applied</i> , 2018, 9, .	3.8	12
9	Spin and reoccupation noise in a single quantum dot beyond the fluctuation-dissipation theorem. <i>Physical Review B</i> , 2018, 97, .	3.2	18
10	p+/n+ polysilicon-on-oxide tunneling junctions as an interface of p-type PERC cells for tandem applications. , 2018, , .		0
11	Hole-capture competition between a single quantum dot and an ionized acceptor. <i>Physical Review B</i> , 2018, 98, .	3.2	5
12	Electron g-factor fluctuations in highly doped GaAs at high temperatures detected by ultrafast spin noise spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600574.	1.5	3
13	Time-Resolved Spin Dynamics and Spin Noise Spectroscopy. <i>Springer Series in Solid-state Sciences</i> , 2017, , 131-154.	0.3	0
14	Closing the gap between spatial and spin dynamics of electrons at the metal-to-insulator transition. <i>Physical Review B</i> , 2017, 96, .	3.2	12
15	Thermodynamic origin of the slow free exciton photoluminescence rise in GaAs. <i>Physical Review B</i> , 2016, 93, .	3.2	14
16	Comment on "Two-Dimensional Optical Control of Electron Spin Orientation by Linearly Polarized Light in InGaAs". <i>Physical Review Letters</i> , 2016, 117, 139701.	7.8	1
17	Interplay of Electron and Nuclear Spin Noise in mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>n</mml:mi></mml:mrow></mml:math>-Type GaAs. <i>Physical Review Letters</i> , 2015, 115, 176601.	7.8	33
18	Growth and characterization of sidewall graphene nanoribbons. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	29

#	ARTICLE	IF	CITATIONS
19	The rise of spin noise spectroscopy in semiconductors: From acoustic to GHz frequencies. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 1824-1838.	1.5	78
20	Spin noise spectroscopy in semiconductors: from a billion down to single spins. <i>Proceedings of SPIE</i> , 2014, , .	0.8	7
21	Optical Spin Noise of a Single Hole Spin Localized in an (InGa)As Quantum Dot. <i>Physical Review Letters</i> , 2014, 112, 156601.	7.8	55
22	Effect of symmetry reduction on the spin dynamics of (001)-oriented GaAs quantum wells. <i>Physical Review B</i> , 2013, 87, .	3.2	13
23	Spin noise spectroscopy of donor-bound electrons in ZnO. <i>Physical Review B</i> , 2013, 87, .	3.2	17
24	Rapid scanning of spin noise with two free running ultrafast oscillators. <i>Optics Express</i> , 2013, 21, 5872.	3.4	17
25	Spin noise spectroscopy of ZnO. , 2013, , .	0	
26	Ultrahigh Bandwidth Spin Noise Spectroscopy: Detection of Large Δg -Factor Fluctuations in Highly-Doped GaAs. <i>Physical Review Letters</i> , 2013, 111, 186602.	7.8	27
27	Measurement of heavy-hole spin dephasing in (InGa)As quantum dots. <i>Applied Physics Letters</i> , 2012, 100, 031906.	3.3	41
28	Spin noise spectroscopy: hole spin dynamics in semiconductor quantum dots. , 2012, , .	2	
29	Electron spin orientation under in-plane optical excitation in GaAs quantum wells. <i>Physical Review B</i> , 2012, 86, .	3.2	4
30	Analyzing atomic noise with a consumer sound card. <i>American Journal of Physics</i> , 2012, 80, 240-245.	0.7	5
31	Electron spin relaxation as tracer of excitons in a two-dimensional electron-hole plasma inside a (110)-GaAs quantum well. <i>Europhysics Letters</i> , 2011, 96, 67010.	2.0	4
32	Electron-gauge factor anisotropy in symmetric (110)-oriented GaAs quantum wells. <i>Physical Review B</i> , 2011, 84, .	3.2	16
33	Spin-orbit fields in asymmetric (001)-oriented GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 2011, 83, .	3.2	47
34	Spin-noise spectroscopy under resonant optical probing conditions: Coherent and nonlinear effects. <i>Physical Review A</i> , 2011, 84, .	2.5	23
35	Strain-induced spin relaxation anisotropy in symmetric (001)-oriented GaAs quantum wells. <i>Physical Review B</i> , 2011, 84, .	3.2	13
36	Efficient data averaging for spin noise spectroscopy in semiconductors. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	14

#	ARTICLE	IF	CITATIONS
37	Semiconductor spin noise spectroscopy: Fundamentals, accomplishments, and challenges. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 43, 569-587.	2.7	102
38	Electron-spin relaxation in bulk GaAs for doping densities close to the metal-to-insulator transition. <i>Physical Review B</i> , 2010, 81, .	3.2	64
39	Gigahertz spin noise spectroscopy in $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">\langle mml:mi>n\langle mml:mi\rangle\langle mml:math>$ -doped bulk GaAs. <i>Physical Review B</i> , 2010, 81, .	3.2	31
40	Temperature-dependent electron Landâ© $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">\langle mml:mi>g\langle mml:mi\rangle\langle mml:math>$ factor and the interband matrix element of GaAs. <i>Physical Review B</i> , 2009, 79, .	3.2	44
41	Towards Bose-Einstein Condensation of Semiconductor Excitons: The Biexciton Polarization Effect. <i>Physical Review Letters</i> , 2009, 103, 146402.	7.8	4
42	Spatially resolved doping concentration measurement in semiconductors via spin noise spectroscopy. <i>Applied Physics Letters</i> , 2009, 94, 112105.	3.3	34
43	Spin noise spectroscopy in semiconductors. <i>Proceedings of SPIE</i> , 2009, , .	0.8	0
44	Optical orientation in quantum wells. <i>Semiconductor Science and Technology</i> , 2008, 23, 114006.	2.0	2
45	High temperature electron spin relaxation in bulk GaAs. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	52
46	Spin Noise Spectroscopy in GaAs (110) Quantum Wells: Access to Intrinsic Spin Lifetimes and Equilibrium Electron Dynamics. <i>Physical Review Letters</i> , 2008, 101, 206601.	7.8	111
47	Ferromagnet/Semiconductor Heterostructures and Spininjection. <i>Springer Tracts in Modern Physics</i> , 2008, , 335-360.	0.1	5
48	Spin noise spectroscopy in semiconductors. <i>Review of Scientific Instruments</i> , 2007, 78, 103903.	1.3	63
49	Comment on âœElectrically injected spin-polarized vertical-cavity surface-emitting lasersâ•[Appl. Phys. Lett. 87, 091108 (2005)]. <i>Applied Physics Letters</i> , 2006, 88, 056101.	3.3	7
50	Design considerations for semiconductor spin lasers. <i>Superlattices and Microstructures</i> , 2005, 37, 306-312.	3.1	17
51	Optical orientation of electron spins in GaAs quantum wells. <i>Physical Review B</i> , 2005, 71, .	3.2	83
52	Spin Noise Spectroscopy in GaAs. <i>Physical Review Letters</i> , 2005, 95, 216603.	7.8	159
53	Room-temperature threshold reduction in vertical-cavity surface-emitting lasers by injection of spin-polarized electrons. <i>Applied Physics Letters</i> , 2005, 87, 241117.	3.3	94
54	Anomalous Spin Dephasing in (110) GaAs Quantum Wells: Anisotropy and Intersubband Effects. <i>Physical Review Letters</i> , 2004, 93, 147405.	7.8	146

#	ARTICLE		IF	CITATIONS
55	Anomalous spin dephasing in (110) GaAs quantum wells. , 2004, , .		1	
56	Circular photogalvanic effect at inter-band excitation in semiconductor quantum wells. Solid State Communications, 2003, 128, 283-286.		1.9	61
57	Laser threshold reduction in a spintronic device. Applied Physics Letters, 2003, 82, 4516-4518.		3.3	178
58	Magnetoelectronics enhance memory. Physics World, 2003, 16, 20-21.		0.0	1
59	Spin injection, spin transport and spin coherence. Semiconductor Science and Technology, 2002, 17, 285-297.		2.0	49
60	Quantifying the drift velocity of carrier ensembles in time-dependent electric fields. Journal of Applied Physics, 2002, 91, 9869.		2.5	2
61	Spin-Dependent Energy Transfer from Exciton States into the Mn ²⁺ (3d5) Internal Transitions. Physica Status Solidi (B): Basic Research, 2002, 229, 781-785.		1.5	14
62	Spin-Dependent Energy Transfer from Exciton States into the Mn ²⁺ (3d5) Internal Transitions. , 2002, 229, 781.		1	
63	Spintronics: Spin Electronics and Optoelectronics in Semiconductors. , 2001, , 173-186.		26	
64	Time-Resolved Fluorescence in 3-Dimensional Ordered Columnar Discotic Materials. Journal of Physical Chemistry B, 2001, 105, 4596-4602.		2.6	10
65	Dispersive Relaxation Dynamics of Photoexcitations in a Polyfluorene Film Involving Energy Transfer: Experiment and Monte Carlo Simulations. Journal of Physical Chemistry B, 2001, 105, 9139-9149.		2.6	154
66	Interchromophoric Coupling in Oligo(p-phenylenevinylene)-Substituted Poly(propyleneimine) Dendrimers. Journal of Physical Chemistry A, 2001, 105, 10220-10229.		2.5	28
67	Injection of spin for electronics. Physics World, 2001, 14, 23-24.		0.0	0
68	Coherent dynamics of coupled electron and hole spins in semiconductors. Solid State Communications, 2001, 120, 73-78.		1.9	17
69	Time-resolved fluorescence studies and Monte Carlo simulations of relaxation dynamics of photoexcitations in a polyfluorene film. Chemical Physics Letters, 2001, 339, 223-228.		2.6	58
70	Spintronics: Spin Electronics and Optoelectronics in Semiconductors. Lecture Notes in Physics, 2001, , 181-194.		0.7	0
71	Excitons, or No Excitons, That Is the Question. Physica Status Solidi A, 2000, 178, 27-32.		1.7	13
72	Motional Narrowing in the Spin Relaxation of Free Excitons?. Physica Status Solidi A, 2000, 178, 531-534.		1.7	2

#	ARTICLE	IF	CITATIONS
73	Carrier-Relaxation Process in Time-Resolved Up-Converted Photoluminescence at Ordered (Al _{0.5} Ga _{0.5}) _{0.5} In _{0.5} P and GaAs Heterointerface. Japanese Journal of Applied Physics, 1999, 38, 1001-1003.	1.5	2
74	Cooling dynamics of excitons in GaN. Physical Review B, 1999, 59, R7797-R7800.	3.2	19
75	Relation between spin and momentum relaxation in ZnSe/ZnMgSSe quantum wells. Physica B: Condensed Matter, 1999, 272, 338-340.	2.7	8
76	When do excitons really exist?. Physica B: Condensed Matter, 1999, 272, 328-330.	2.7	18
77	The dynamics of gain-narrowing in a ladder-type π -conjugated polymer. Chemical Physics Letters, 1999, 312, 376-384.	2.6	31
78	Relaxation dynamics of excitons in thin quaterthiophene films on different substrates. Chemical Physics Letters, 1999, 314, 9-15.	2.6	22
79	Injecting spin into electronics. Nature, 1999, 402, 735-736.	27.8	77
80	Conjugated polymer lasers: emission characteristics and gain mechanism. Physical Chemistry Chemical Physics, 1999, 1, 1795-1800.	2.8	11
81	Spin injection into semiconductors. Applied Physics Letters, 1999, 74, 1251-1253.	3.3	218
82	Spinning electrons could lead electronics revolution. Physics World, 1999, 12, 22-22.	0.0	2
83	Pulsed Vertical-Cavity-Laser Emission Synchronized to Electron Spin Precession. Physica Status Solidi (B): Basic Research, 1998, 206, 387-398.	1.5	1
84	Direct observation of the rotational direction of electron spin precession in semiconductors. Solid State Communications, 1998, 108, 753-758.	1.9	7
85	Disorder influenced optical properties of \pm -sexithiophene single crystals and thin evaporated films. Chemical Physics, 1998, 227, 49-56.	1.9	54
86	Spin transport in GaAs. Applied Physics Letters, 1998, 73, 1580-1582.	3.3	203
87	Pump geometry for resonant and quasi-resonant optical excitation of microcavity lasers. Optics Letters, 1998, 23, 849.	3.3	0
88	Hanle-oscillations in the stimulated emission of microcavity laser. , 1998, , 245-255.		2
89	Spinquantenschwebungen in Halbleitern " der Hanle-Effekt zeitaufgelöst. Physik Journal, 1998, 54, 49-52.	0.1	2
90	Influence of carrier relaxation on the dynamics of stimulated emission in microcavity lasers. Applied Physics Letters, 1997, 71, 3761-3763.	3.3	11

#	ARTICLE	IF	CITATIONS
91	Manifestation of coherent spin precession in stimulated semiconductor emission dynamics. <i>Physical Review B</i> , 1997, 56, R7076-R7079.	3.2	125
92	Influence of Carrier Cooling on the Emission Dynamics of Semiconductor Microcavity Lasers. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 204, 548-551.	1.5	0
93	Electron and hole g-factors in CdTe/CdMgTe quantum wells. <i>Applied Physics Letters</i> , 1996, 69, 3704-3706.	3.3	28
94	Vacuum field induced mixing of light and heavy-hole excitons in a semiconductor microcavity. <i>Applied Physics Letters</i> , 1996, 69, 3465-3467.	3.3	5
95	Spin quantum beats in semiconductors. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1996, 2, 747-755.	2.9	48
96	Carrier relaxation and electronic structure in InAs self-assembled quantum dots. <i>Physical Review B</i> , 1996, 54, 11346-11353.	3.2	200
97	<title>Excited states in InAs self-assembled quantum dots</title>, 1996, 2694, 185.		2
98	Magnetoluminescence studies of InAl _{1-y} As self-assembled quantum dots in Al _x Ga _{1-x} As matrices. <i>Physical Review B</i> , 1996, 53, 16458-16461.	3.2	63
99	Temperature and density dependence of the electron Landé g-factor in semiconductors. <i>Physical Review B</i> , 1996, 53, 7911-7916.	3.2	119
100	Time-resolved luminescence of semiconductor heterostructures in high magnetic fields. <i>Physica B: Condensed Matter</i> , 1995, 204, 332-338.	2.7	2
101	Electron g factor in quantum wells determined by spin quantum beats. <i>Solid State Communications</i> , 1995, 93, 313-317.	1.9	95
102	Dynamics of exciton relaxation and excitation transfer to donor-bound excitons in CdTe/CdMnTe quantum wells. <i>Journal of Applied Physics</i> , 1995, 78, 451-456.	2.5	6
103	Extreme Anisotropy of the <i>g</i>-Factor in Quantum Wires. <i>Europhysics Letters</i> , 1995, 31, 399-404.	2.0	30
104	Temperature Dependence of the Electron Landé g Factor in GaAs. <i>Physical Review Letters</i> , 1995, 74, 2315-2318.	7.8	124
105	Relaxation of excitons in corrugated GaAs/AlAs superlattices. <i>Physical Review B</i> , 1994, 49, 10786-10789.	3.2	11
106	Landau versus one-dimensional quantization in GaAs. <i>Journal of Luminescence</i> , 1994, 60-61, 390-392.	3.1	8
107	Reduced exciton-exciton scattering in quantum wires. <i>Journal of Luminescence</i> , 1994, 58, 120-122.	3.1	2
108	Picosecond spectroscopy of plastically deformed GaAs. <i>Journal of Luminescence</i> , 1994, 58, 123-126.	3.1	1

#	ARTICLE	IF	CITATIONS
109	Direct observation of resonant tunneling dynamics in high magnetic fields. Physical Review Letters, 1994, 72, 1522-1525.	7.8	12
110	Exciton radiative decay and homogeneous broadening in CdTe/Cd0.85Mn0.15Te multiple quantum wells. Physical Review B, 1993, 48, 8980-8985.	3.2	46
111	Reduced exciton-exciton scattering in quantum wires. Physical Review Letters, 1993, 70, 1682-1684.	7.8	34
112	Coherent dynamics of coupled electron and hole spins in semiconductors. , 0, , .	0	
113	Spin relaxation in n-doped GaAs/AlGaAs quantum wells. , 0, , .	1	
114	Electron Spin Relaxation in Semiconductors. , 0, , 253-261.	18	
115	How to Make Nanosheets Glow: An Innovative Route to Photoluminescent Colloidal 2D TMDCs. , 0, , .	0	